NPN 100mA 50V Digital Transistors (Bias Resistor Built-in Transistors)



Parameter	Value
$V_{\sf CEO}$	50V
I _C	100mA
R ₁	47kΩ

Features

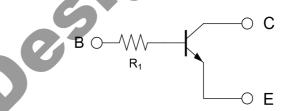
ROHM

- 1) Built-In Biasing Resistor
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 3) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- Only the on/off conditions need to be set for operation, making the circuit design easy.
- 5) Complementary PNP Types: DTA144T series
- 6) Complex transistors: UMH14N/ IMH14A/ EMH15/ IMH15A (NPN type)
- 7) Lead Free/RoHS Compliant.

Outline



•Inner circuit



Application

Switching circuit, Inverter circuit, Interface circuit,

Driver circuit

B: BASE

C: COLLECTOR

E: EMITTER

Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
DTC144TM	VMT3	1212	T2L	180	8	8000	06
DTC144TE	EMT3	1616	TL	180	8	3000	06
DTC144TUA	UMT3	2021	T106	180	8	3000	06
DTC144TKA	SMT3	2928	T146	180	8	3000	06

● Absolute maximum ratings (T_a = 25°C)

Pa	arameter	Symbol	Values	Unit	
Collector-base voltage		V_{CBO}	V _{CBO} 50		
Collector-emitter voltage			50	V	
Emitter-base voltage	Emitter-base voltage V _{EBO} 5			V	
Collector current	Collector current I _C 100			mA	
	DTC144TM		150		
Dower discipation	DTC144TE	D *1	150		
Power dissipation	DTC144TUA	P _D *1	200	mW	
	DTC144TKA		200		
Junction temperature	T	150	°C		
Range of storage tempera	ture	T _{stg}	-55 to +150	°C	

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol Conditions		Values			Unit
Parameter			Min.	Тур.	Max.	OHIL
Collector-base breakdown voltage	BV _{CBO}	$I_C = 50\mu A$	50	-	-	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	50	-	-	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 50μA	5	-	-	V
Collector cut-off current	I _{CBO}	V _{CB} = 50V	-	-	0.5	μA
Emitter cut-off current	EBO	V _{EB} = 4V	-	-	0.5	μA
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{C} / I_{B} = 5 \text{mA} / 0.5 \text{mA}$	-	-	0.3	V
DC current gain	h _{FE}	$V_{CE} = 5V$, $I_{C} = 1mA$	100	250	600	-
Input resistance	R_1	-	32.9	47	61.1	kΩ
Transition frequency	f _T *2	$V_{CE} = 10V, I_{E} = -5mA,$ f = 100MHz	-	250	-	MHz

^{*1} Each terminal mounted on a reference footprint

^{*2} Characteristics of built-in transistor

● Electrical characteristic curves(Ta=25°C)

Fig.1 Grounded emitter propagation characteristics

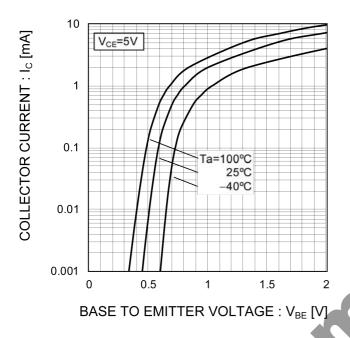


Fig.2 Grounded emitter output characteristics

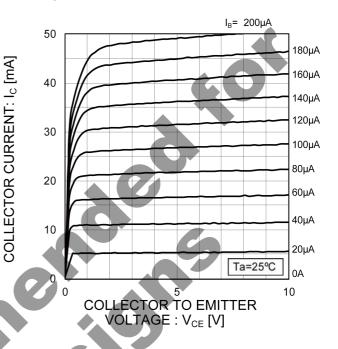


Fig.3 DC Current gain vs. Collector Current

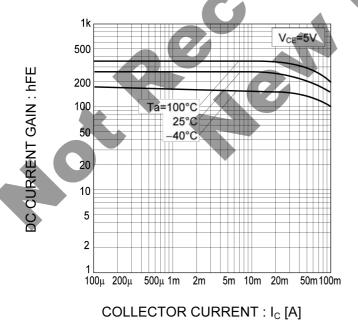
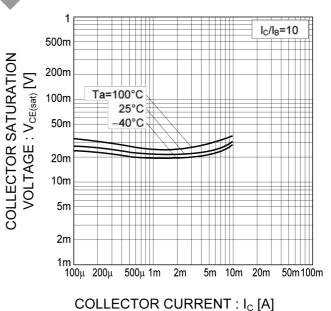


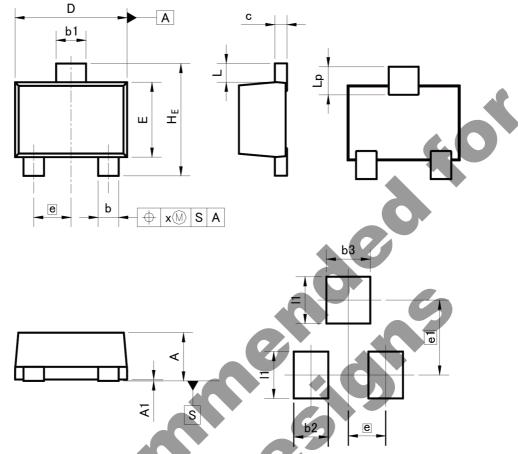
Fig.4 Collector-emitter saturation voltage vs.

Collector Current



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Pattern of terminal position areas [Not a recommended pattern of soldering pads]

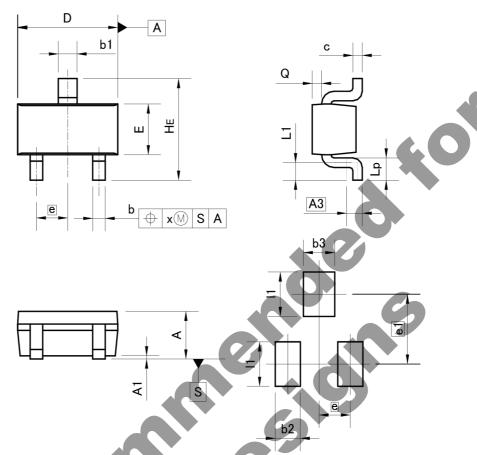
DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	0.45	0.55	0.018	0.022
A1	0.00	0.10	0.000	0.004
b	0.17	0.27	0.007	0.011
b1	0.27	0.37	0.011	0.015
С	0.08	0.18	0.003	0.007
D	1.10	1.30	0.043	0.051
Ē	0.70	0.90	0.028	0.035
е	0.	40	0.0	02
HE	1.10	1.30	0.043	0.051
L	0.10	0.30	0.004	0.012
Lp	0.20	0.40	0.008	0.016
×	42	0.10	=	0.004

DIM MILIM	ETERS	INC	HES	
	MIN	MAX	MIN	MAX
b2	=	0.37		0.015
b3		0.47	100	0.019
e1	0.80		0.0	031
11	-	0.50	-	0.020

Dimension in mm/inches



EMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

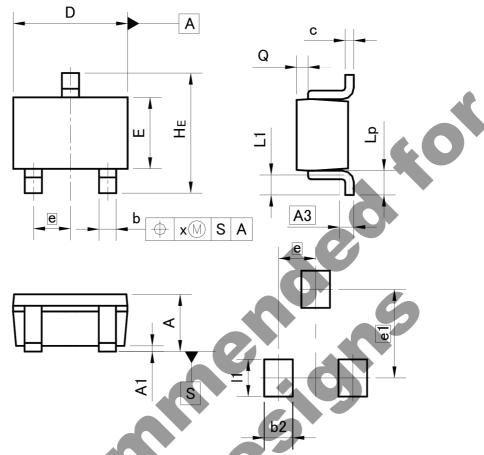
DIM	MILIME	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	0.60	0.80	0.024	0.031
A1	0.00	0.10	0.000	0.004
A3	0.	25	0.0	10
Ь	0.15	0.30	0.006	0.012
b1	0.25	0.40	0.010	0.016
C	0.10	0.20	0.004	0.008
D	1.50	1.70	0.059	0.067
E	0.70	0.90	0.028	0.035
е	0.8	50	0.0	20
HE	1.40	1.80	0.055	0.071
L1	0.10	#8	0.004	, 3
Lp	0.15	52	0.006	EL.
Q	0.05	0.25	0.002	0.010
×	=7	0.10	= 1	0.004

DIM	DIM	MILIMETERS		INC	HES
	MIN	MAX	MIN	MAX	
b2	₹7.1t	0.40		0.016	
b3		0.50	-	0.020	
e1	1.10		0.0	043	
11	42 55	0.70	-	0.028	

Dimension in mm/inches



UMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

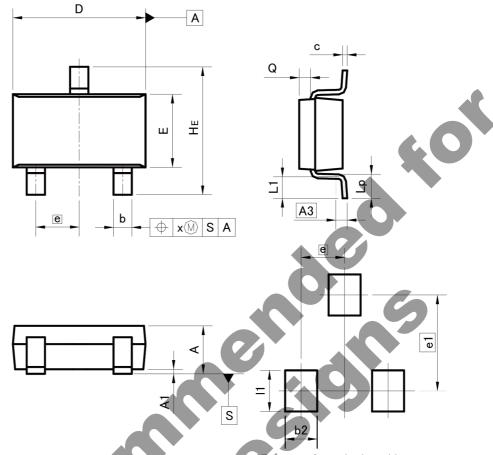
DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	0.80	1.00	0.031	0.039
A1	0.00	0.10	0.000	0.004
A3	0.3	25	0.0	10
ь	0.15	0.30	0.006	0.012
С	0.10	0.20	0.004	0.008
D	1.90	2.10	0.075	0.083
E	1.15	1.35	0.045	0.053
е	0.65 0.026		026	
HE	2.00	2.20	0.079	0.087
L1	0.20	0.50	0.008	0.020
Lp	0.25	0.55	0.010	0.022
Q	0.10	0.30	0.004	0.012
×	=	0.10	=	0.004

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
b2		0.50	_	0.020
e1	1.55		0.0	061
11	_	0.65	_	0.026

Dimension in mm/inches



SMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
A	1.00	1.30	0.039	0.051
(A1	0.00	0.10	0.000	0.004
A3	0	25	0.0	10
b	0.35	0.50	0.014	0.020
С	0.09	0.25	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
е	0.9	95	0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lр	0.40	0.70	0.016	0.028
Q	0.20	0.30	0.008	0.012
X	2	0.10	1 <u>20</u> 1	0.004
У	27	0.10	_	0.004
				-
DIM	MILIM	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
60	1505	0.00		0.004

DIM	MILIMETERS		DIM MILIMETE		INC	HES
DIM	MIN	MAX	MIN	MAX		
b2	=	0.60		0.024		
e1	2.10		0.0	083		
11	=:	0.90	-	0.035		

Dimension in mm/inches



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